# Study on barium titanate ceramics prepared by various methods

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Barium titanate (BaTiO<sub>3</sub>) ceramics have been fabricated using powders prepared by sol-gel, coprecipitation and mixed oxide methods. The powders prepared by sol-gel and coprecipitation have average crystallite diameters of 100 nm and 300 nm, respectively while the diameter of the mixed oxide powder is  $\sim$ 1–3  $\mu$ m. When sintered at the same temperature of 1320°C, the three BaTiO<sub>3</sub> ceramics have very different grain size, with the one prepared by the mixed oxide method having the largest grain size of 20  $\mu$ m. The dielectric permitivity increases as the grain size of the ceramic becomes smaller. The room temperature (25°C) dielectric permittivity, pyroelectric and piezoelectric properties of these ceramics have been measured as functions of the poling field. The BaTiO<sub>3</sub> ceramic fabricated from nanosized powder derived from the coprecipitation method is found to have the smallest grain size and better properties than prepared from the sol-gel route, and is thus a good candidate for use in devices that required thick (10 to 20  $\mu$ m) ferroelectric films. © *2001 Kluwer Academic Publishers* 

# 1. Introduction

Since the discovery of barium titanate (BaTiO<sub>3</sub>) in the early 1940's, there has been a continuous development of using it in new industrial and commercial applications. BaTiO<sub>3</sub> is widely used as capacitors, ultrasonic transducers, pyroelectric infrared sensors and positive temperature coefficient (PTC) resistors [1–4]. Being a lead-free ferroelectric ceramic, BaTiO<sub>3</sub> is an environmentally friendly material, thus making it a good candidate for various applications.

In order to prepare BaTiO<sub>3</sub> ceramic thick films (10–20  $\mu$ m) for use in various devices, the ceramic is required to have small grain size and reasonably good properties. BaTiO<sub>3</sub> ceramic prepared from the conventional mixed oxide route has too large (>10  $\mu$ m) a grain size for thick film applications. In the present study, BaTiO<sub>3</sub> powders prepared by the sol-gel process [5] and the coprecipitation method [6] are sintered at various temperatures to give ceramics with small grain size, the properties of which are then compared with those of BaTiO<sub>3</sub> ceramics prepared by the mixed oxide route [7]. In the following sections, BaTiO<sub>3</sub> (sol-gel), BaTiO<sub>3</sub> (coprecipitation) and BaTiO<sub>3</sub> (oxide) denote the ceramic samples prepared by sintering powder obtained from the sol-gel process, coprecipitation method and mixed oxide method, respectively. The dielectric permittivity, pyroelectric and piezoelectric properties of BaTiO<sub>3</sub> ceramics prepared by various methods are investigated.

# 2. Sample preparation and experiments

Nanosized BaTiO<sub>3</sub> powder was prepared either by the sol-gel process or by the coprecipitation method. In the

sol-gel process (Fig. 1), barium acetate and titanium isopropoxide were dissolved in deionized water and then mixed under continuous stirring at room temperature ( $25 \,^{\circ}$ C). The amounts of barium acetate and titanium isopropoxide were in a molar ratio of 1 : 1. In order to avoid precipitation, small amounts of acetic acid and acetylacetone were added. The sol was relatively stable and became a gel in a few days. The BaTiO<sub>3</sub> gel was dried at 100 °C for 24 h and then annealed at 800 °C for 24 h to give BaTiO<sub>3</sub> powder. The average crystallite size of the annealed powder was about 100 nm as determined by X-ray diffraction.

The BaTiO<sub>3</sub> powder prepared by coprecipitation method was supplied by the Shanghai Institute of Ceramics. In the coprecipitation process, a mixed solution of barium chloride and titanium tetrachloride was added drop by drop into oxalic acid while being vigorously stirred. The amounts of barium chloride and titanium tetrachloride were in a molar ratio of 1:1. The amount of oxalic acid used was 20% in excess of the stoichiometric amount required to give precipitates. The resulting BaTiO<sub>3</sub> precipitates were washed repeatedly in deionized water and then dried at 80 °C. The crystallite size of the powder was about 300 nm.

The BaTiO<sub>3</sub> powder prepared by the mixed oxide route was provided by Zhongshan University in Guangzhou. The BaTiO<sub>3</sub> powder was prepared by reacting BaCO<sub>3</sub> and TiO<sub>2</sub> in air. BaTiO<sub>3</sub> was initially formed at the BaCO<sub>3</sub>-TiO<sub>2</sub> grain boundaries. Then BaTiO<sub>3</sub> reacted with BaCO<sub>3</sub> to form Ba<sub>2</sub>TiO<sub>4</sub> until all the BaCO<sub>3</sub> was exhausted. Finally Ba<sub>2</sub>TiO<sub>4</sub> reacted with the remaining TiO<sub>2</sub> to form BaTiO<sub>3</sub>. The size of the powder was between 1 to 3  $\mu$ m.



*Figure 1* Flowchart showing the procedures for preparing  $BaTiO_3$  powder by a sol-gel process.

The BaTiO<sub>3</sub> powders prepared by the above three methods were pressed into discs and sintered at various temperatures for 1 h to give the ceramic samples.

The structures of the samples were studied by scanning electron microscopy (Leica Steroscan 440) and X-ray diffraction (Philips X'pert XRD System). For electrical measurements, air-dried silver paint was applied to both sides of each sample to serve as electrodes. The relative permittivity  $\varepsilon'$  and dielectric loss tan  $\delta$  at 1 kHz were measured using a HP4194A impedance analyzer. After the BaTiO<sub>3</sub> samples had been poled at various d.c. fields, the pyroelectric coefficient *p* was measured using the digital integration method [8] and the piezoelectric coefficient  $d_{33}$  was measured by a Pennebaker model 8000 piezo  $d_{33}$  tester (American Piezo-Ceramic Inc.). A HP4194A impedance analyzer was used to measure the thickness electromechanical coupling coefficient  $k_t$  by a resonance technique following the IEEE standard [9].

### 3. Experimental results

### 3.1. Structures and microstructures

Figs 2–4 show the SEM micrographs of  $BaTiO_3$  (sol-gel),  $BaTiO_3$  (coprecipitation) and  $BaTiO_3$  (oxide), respectively. For the SEM measurements, the

TABLE I Showing the variations of grain size, tetragonality (c/a) and density with sintering temperature for BaTiO<sub>3</sub> ceramics prepared by different methods

Synthesis method	Sintering temperature (°C)	Average grain size (µm)	c/a ratio	Density (kg/m <sup>3</sup> )
Sol-gel	1150	2	1.009	5574
	1200	5	1.010	5649
	1320	10	1.010	5685
Coprecipitation	1250	0.60	1.006	5250
	1280	0.72	1.007	5400
	1300	0.90	1.008	5510
	1320	1.13	1.009	5706
Mixed oxide	1320	20	1.010	5702



Figure 2 SEM micrographs of BaTiO<sub>3</sub> (sol-gel) ceramic sintered at (a) 1150°C, (b) 1200°C and (c) 1320°C. (Continued.)



Figure 2 (Continued).

ceramics were polished and thermally etched at a temperature 50 °C below the sintering temperature. The average grain size was determined from the SEM micrographs and shown in Table I. For BaTiO<sub>3</sub> (solgel), the grain size of the ceramic increases rapidly as the sintering temperature  $T_s$  increases, reaching 10  $\mu$ m at  $T_s = 1320$ °C (Fig. 2). However, the grain size of BaTiO<sub>3</sub> (coprecipitation) is very small and shows

a much slower increase with sintering temperature, reaching only 1.13  $\mu$ m at  $T_s = 1320^{\circ}$ C (Fig. 3). Following the conventional procedure, BaTiO<sub>3</sub> (oxide) was sintered only at 1320°C. This results in a grain size much larger than those in BaTiO<sub>3</sub> (sol-gel) and BaTiO<sub>3</sub> (coprecipitation) (Fig. 4).

Fig. 5 shows the XRD patterns of  $BaTiO_3$  (coprecipitation) sintered at 1320 °C. Although not shown,





Figure 3 SEM micrographs of BaTiO<sub>3</sub> (coprecipitation) ceramic sintered at (a) 1250°C, (b) 1280°C and (c) 1300°C and (d) 1320°C. (Continued.)

the XRD patterns of BaTiO<sub>3</sub> (sol-gel) and BaTiO<sub>3</sub> (oxide) are very similar to that shown in Fig. 5 showing that perovskite structure has been formed. The tetragonality (c/a ratio) are obtained from the XRD patterns and shown in Table I. The tetragonality of both BaTiO<sub>3</sub> (sol-gel) and BaTiO<sub>3</sub> (coprecipitation) increases as  $T_s$  increases and saturates at 1.010, a value closed to the reported value [10–12]. The densities of the ceramic samples are also given in Table I. In subsequent work, properties of BaTiO<sub>3</sub> (sol-gel), BaTiO<sub>3</sub> (coprecipitation) and BaTiO<sub>3</sub> (oxide) sintered at 1320 °C are reported and compared.





Figure 3 (Continued).

# 3.2. Dielectric, pyroelectric and piezoelectric properties

All BaTiO<sub>3</sub> samples were poled at 90 °C in an oil bath by applying various d.c. fields. After poling, the samples were annealed in a short-circuited condition at 50 °C for 3 h before measurements. This process can eliminate the contribution of thermally stimulated current in subsequent measurements. The dielectric permittivity  $\varepsilon$  and loss tan  $\delta$  of the samples were measured before poling. The samples were poled using different poling fields and as the poling field increases,  $\varepsilon'$  decrease (Fig. 6) which may be due to the domain orientation after poling. As the grain size of the ceramic decreases (Table I),  $\varepsilon'$  increases (Table II), which exhibit a grain size effect similar to that reported in the literature [10, 11].



Figure 4 SEM micrograph of BaTiO<sub>3</sub> (oxide) ceramic sintered at 1320°C.

TABLE II Properties of BaTiO<sub>3</sub> ceramics after being poled with E = 5 kV/mm at 90 °C

Synthesis method	Sol-gel	Coprecipitation	Mixed oxide
Sintering temperature (°C)	1320	1320	1320
Pyroelectric coefficient $p (\mu C/m^2 K)$	121	157	235
Piezoelectric coefficient $d_{33}$ (PC/N)	117	143	175
Thickness electromechanical coupling coefficient $k_t$	0.16	0.22	0.25
Dielectric permittivity $\varepsilon'$ (1 kHz, before poling)	1825	1941	1160
Dielectric loss tan $\delta$ (1 kHz, before poling)	0.04	0.04	0.02

The pyroelectric coefficient p and piezoelectric coefficient  $d_{33}$  of the BaTiO<sub>3</sub> ceramics were measured at 25 °C as functions of the poling field in Figs 7 and 8, respectively. Both p and  $d_{33}$  increase as the poling field increases and tend to saturate when the poling field is above 3 kV/mm. The maximum attainable p and  $d_{33}$ are given in Table II. BaTiO<sub>3</sub> (oxide) has the maximum p and  $d_{33}$  which are closed to the reported values of  $p = 200 \ \mu\text{C/m}^2\text{K}$  and  $d_{33} = 190 \ \text{pC/N}$  [7, 12]. Fig. 9 shows the relationship between the thickness electromechanical coupling coefficient  $k_t$  and the poling field. Similar to p and  $d_{33}$ ,  $k_t$  increases as the poling field increases and tends to saturate when the samples is poled above E = 3 kV/mm. The maximum attainable  $k_t$ are also given in Table II. However, the measured  $k_t$  of the BaTiO<sub>3</sub> ceramics is smaller than the reported value  $(k_t \sim 0.35 [1, 7])$ . BaTiO<sub>3</sub> (coprecipitation) has  $k_t$  close to BaTiO<sub>3</sub> (oxide) and is higher than that of BaTiO<sub>3</sub> (sol-gel).



Figure 5 XRD patterns of  $BaTiO_3$  (coprecipitation) ceramic sintered at  $1320^{\circ}C$ .



*Figure 6* Room temperature dielectric permittivity  $\varepsilon'$  of BaTiO<sub>3</sub> sintered at 1320°C versus poling field.



*Figure 7* Pyroelectric coefficient p of BaTiO<sub>3</sub> sintered at 1320°C versus poling field.



*Figure 8* Piezoelectric coefficient  $d_{33}$  of BaTiO<sub>3</sub> sintered at 1320°C versus poling field.



*Figure 9* Thickness electromechanical coupling coefficient  $k_t$  of BaTiO<sub>3</sub> sintered at 1320°C versus poling field.

#### 4. Conclusion and discussion

 $BaTiO_3$  ceramics have been fabricated using powder prepared by the sol-gel, coprecipitation and conventional mixed oxide methods. Characteristics of  $BaTiO_3$ ceramics prepared by these methods have been investigated. As expected,  $BaTiO_3$  (oxide) has the largest grain size (20  $\mu$ m) and the best properties. The average grain size of BaTiO<sub>3</sub> (sol-gel) sintered at 1320 °C is about 10  $\mu$ m which is too large for thick film applications and it also breaks down easily upon poling. After poling with d.c. field higher than 3 kV/mm, the pyroelectric coefficient p, piezoelectric coefficient  $d_{33}$  and the thickness electromechanical coupling coefficient  $k_t$  of BaTiO<sub>3</sub> (sol-gel) tend to saturate. Although not shown in detail, we found that if BaTiO<sub>3</sub> (sol-gel) was sintered at 1200°C, except for having a smaller grain size (5  $\mu$ m) and a higher dielectric permittivity, the measured values of p,  $d_{33}$  and  $k_t$  are almost identical to BaTiO<sub>3</sub> (sol-gel) sintered at 1320°C showing that there is an upper limit of materials properties which cannot be improved by the grain growth. For BaTiO<sub>3</sub> (coprecipitation), as the sintering temperature increases, the grain grow is very slow. The BaTiO<sub>3</sub> (coprecipitation) sample sintered at 1320°C has an average grain size of 1.13  $\mu$ m which is much smaller than BaTiO<sub>3</sub> (sol-gel) and BaTiO<sub>3</sub> (oxide).

In conclusion, it is found that BaTiO<sub>3</sub> ceramic sintered by using nanosized powder derived from the coprecipitation method has good potential to be used in thick film device applications. BaTiO<sub>3</sub> (coprecipitation) has a smaller grain size, its p and  $d_{33}$  are higher than those of BaTiO<sub>3</sub> (sol-gel) and its  $k_t$  is comparable to that of BaTiO<sub>3</sub> (oxide).

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